

Important notice

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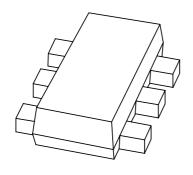
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2015EVLow V_F MEGA Schottky barrier diode

Product data sheet Supersedes data of 2003 May 21 2003 Jun 03



NXP Semiconductors Product data sheet

Low V_F MEGA Schottky barrier diode

PMEG2015EV

FEATURES

Forward current: 1.5 AReverse voltage: 20 V

· Very low forward voltage

• Ultra small plastic SMD package

• Flat leads: excellent coplanarity and improved thermal behaviour.

APPLICATIONS

• Low voltage rectification

• High efficiency DC-DC conversion

• Switch mode power supply

• Inverse polarity protection

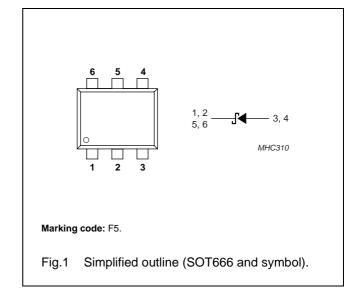
· Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOT666 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		_	20	V
I _F	continuous forward current	T _s < 55 °C	-	1.5	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms square wave; note 1	_	10	Α
I _{FRM}	repetitive peak forward current	$t_p = 1 \text{ ms}; \ \delta = \le 0.25$	-	4.5	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+125	°C

Note

1. Only valid if pins 3 and 4 are connected in parallel.

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	see Fig.2; note 1			
		$I_F = 10 \text{ mA}$	240	270	mV
		I _F = 100 mA	300	350	mV
		I _F = 1000 mA	480	550	mV
		I _F = 1500 mA	530	660	mV
I _R	continuous reverse current	see Fig.3; note 2			
		V _R = 5 V	5	10	μΑ
		V _R = 8 V	7	20	μΑ
		V _R = 15 V	10	50	μΑ
C _d	diode capacitance	$V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$; see Fig.4	19	25	pF

Notes

- 1. Only valid if pins 1, 2 and 5, 6 are soldered on 1 cm² copper solder land.
- 2. Pulse test: $t_p = 300 \ \mu s$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W
R _{th j-s}	thermal resistance from junction to solder point	note 3	80	K/W

Notes

- 1. Refer to SOT666 standard mounting conditions.
- 2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm².
- 3. Soldering point of cathode tabs.

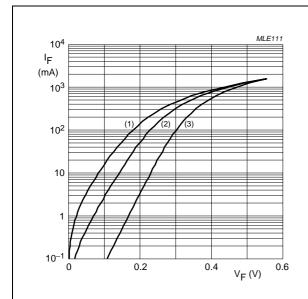
Soldering

Reflow soldering is the only recommended soldering method.

Low V_F MEGA Schottky barrier diode

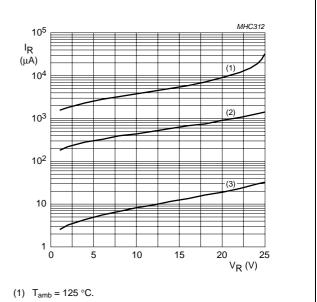
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GRAPHICAL DATA



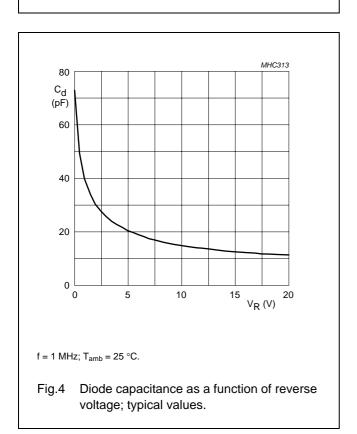
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



NXP Semiconductors Product data sheet

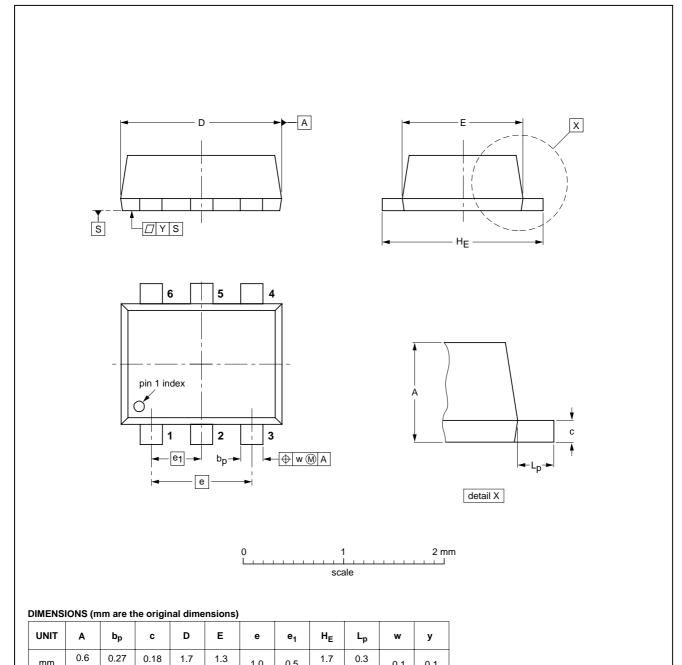
Low V_F MEGA Schottky barrier diode

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						01-01-04 01-08-27

1.5

0.1

1.0

0.5

2003 Jun 03 5

0.17

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: http://www.nxp.com

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